

## isc Silicon NPN Power Transistor

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 400V(Min)
- · Fast Switching Speed
- · Collector-Emitter Saturation Voltage-
- :  $V_{CE(sat)} = 0.7V(Max.)@I_{C} = 3A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

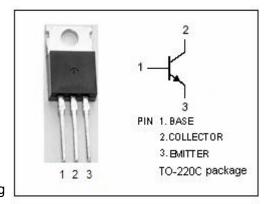
 Designed for use in high-voltage,high-speed,power switching applications such as switching regulators, inverters, solenoid and relay drivers.

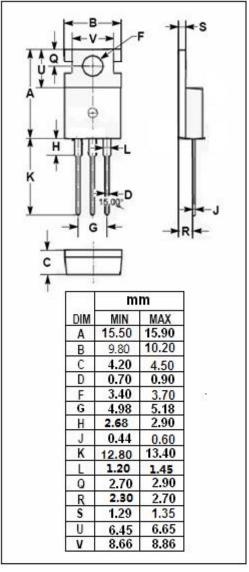


ABOULUTE MAXIMUM NATINGO(1a-20 c)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage 400		V				
V <sub>EBO</sub>	Emitter-Base Voltage 7		V				
Ic	Collector Current-Continuous	lector Current-Continuous 3					
Ісм	Collector Current-Peak	ak 6					
I <sub>B</sub>	Base Current-Continuous	2	А				
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	50	W				
TJ	Junction Temperature	150	$^{\circ}$				
T <sub>stg</sub>	Storage Temperature Range	ange -55~150					

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case		°C/W







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2SC2827

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-200 01	The 35 other wise specified							
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	400			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 3A; I <sub>B</sub> = 0.6A			0.7	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			100	μА		
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 320V; I <sub>B</sub> = 0			100	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			1.0	mA		
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 2V	10					
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.3A; V <sub>CE</sub> = 10V; f= 1MHz	10			MHz		
Switching times								
t <sub>on</sub>	Turn-on Time				1.0	μ \$		
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3A, I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A			2.0	μS		
t <sub>f</sub>	Fall Time				0.5	μS		

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